

POLISHING COMPOSITION

ABSTRACT OF THE DISCLOSURE

A polishing composition of the present invention, to be used in polishing for forming wiring in a semiconductor device, includes: a specific surfactant; a silicon oxide; at least one selected from the group consisting of carboxylic acid and alpha-amino acid; a corrosion inhibitor; an oxidant; and water. This polishing composition is capable of suppressing the occurrence of the dishing.

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Fig. 1 (a)